

**Amendments to the Claims**

Claims 1-50. (Cancelled).

51. (New) A method of forming a capacitor construction comprising:  
forming a capacitor electrode supported by a semiconductor substrate;  
depositing a metal oxide dielectric material over the capacitor electrode;  
providing a precursor at a location proximate the metal oxide dielectric material;  
laser generating at least one activated species from the precursor; and  
after the laser generating, contacting the at least one activated species with the  
dielectric material.

52. (New) The method of claim 51 wherein the metal oxide dielectric material  
comprises one or more of tantalum pentoxide, aluminum pentoxide, hafnium oxide,  
titanium oxide, strontium titanate, barium strontium titanate and silicon oxynitride.

53. (New) The method of claim 51 wherein the at least one activated species  
comprises an activated oxygen species.

54. (New) The method of claim 51 wherein the laser generating comprises  
focusing a laser within a range of locations above an upper surface of the metal oxide  
dielectric layer.

55. (New) The method of claim 54 wherein the range of locations is from about 2 millimeters to about 4 millimeters above the upper surface of the metal oxide dielectric layer.

56. (New) The method of claim 54 wherein the laser produces light having a wavelength of from 193 nm to 248 nm.

57. (New) The method of claim 51 wherein the precursor comprises ozone.